

/ Descriptions

TO-252 PNP Silicon PNP transistor in a TO-252 Plastic Package.

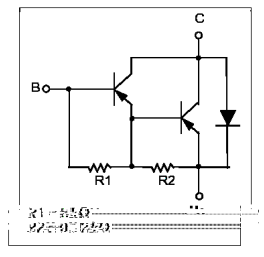
/ Features

TIP122D
Complement to TIP122D.

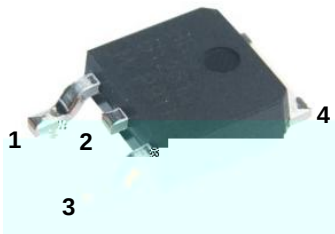
/ Applications

Medium power linear switching applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2,4 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

See Marking Instructions.

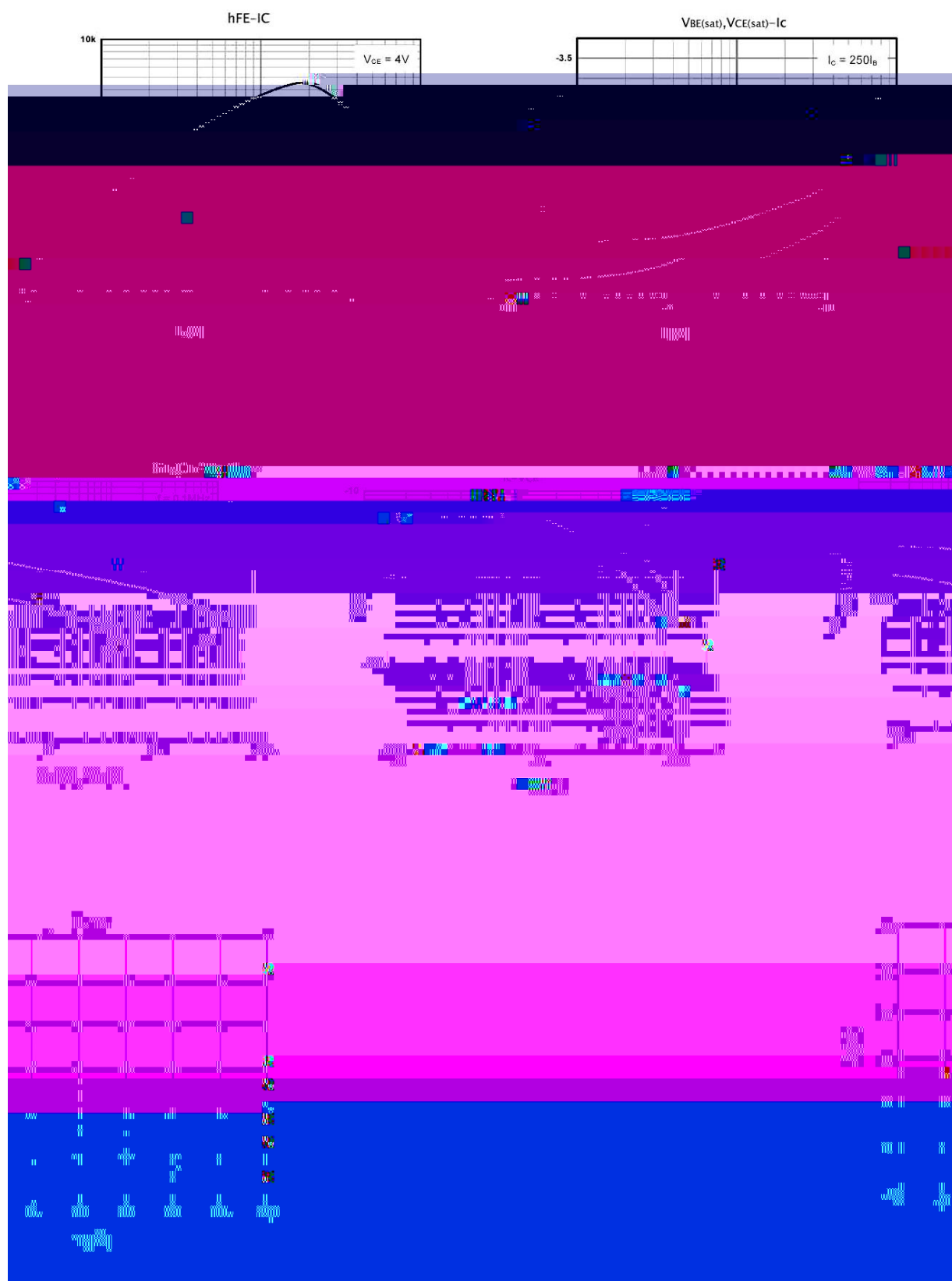
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-5.0	A
Collector Power Dissipation	$P_C(T_C=25)$	40	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

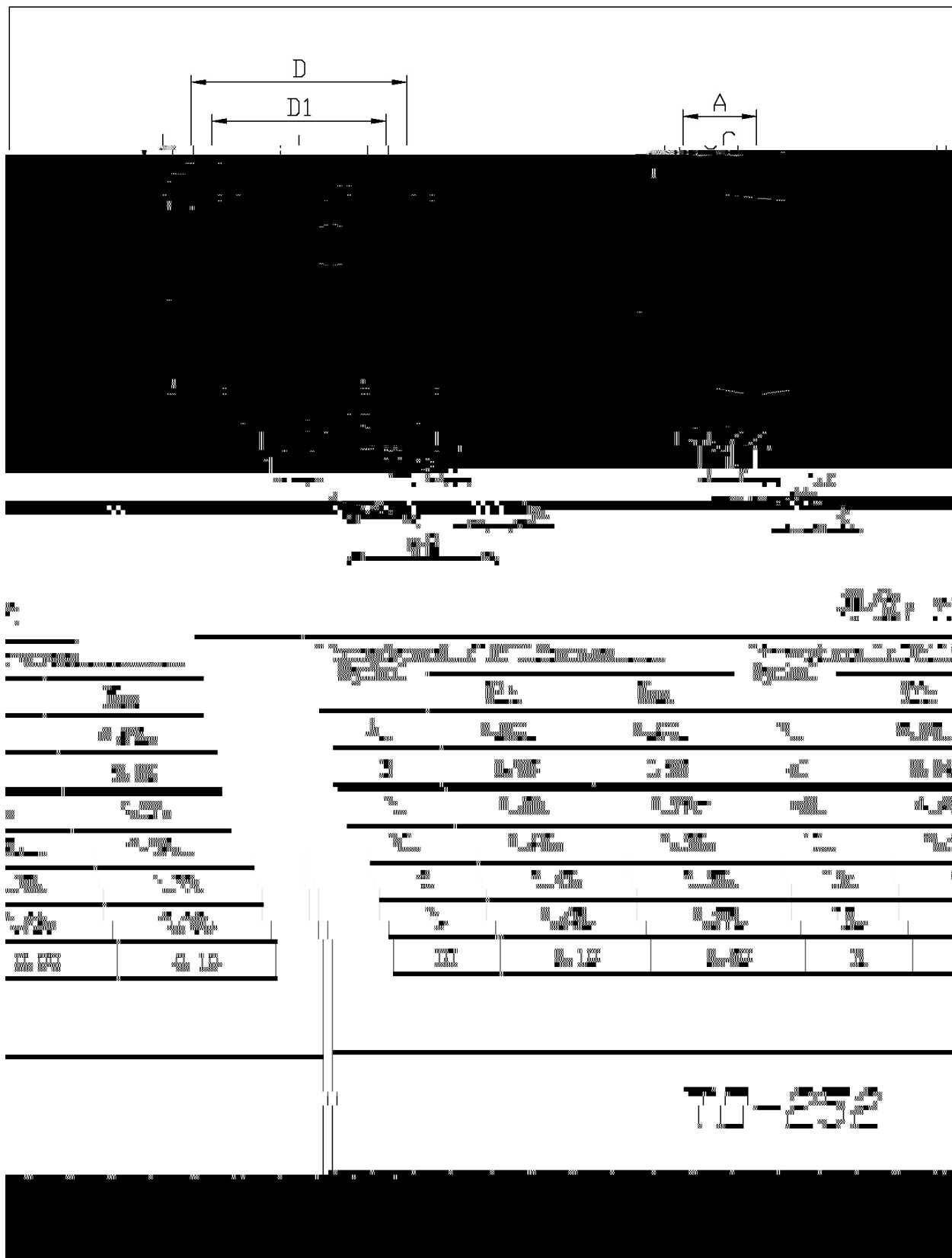
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-100mA$ $I_B=0$	-100			V
Collector Cut-Off Current	I_{CBO}	$V_{CE}=-50V$ $I_B=0$			-2.0	mA
Collector Cut-Off Current	I_{CEO}	$V_{CB}=-100V$ $I_E=0$			-1.0	mA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5.0V$ $I_C=0$			-2.0	mA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-3.0V$ $I_C=-0.5A$	1000			
	$h_{FE(2)}$	$V_{CE}=-3.0V$ $I_C=-3.0A$	1000			
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=-3.0A$ $I_B=-12mA$			-2.0	V
	$V_{CE(sat)(2)}$	$I_C=-5.0A$ $I_B=-20mA$			-4.0	V
Base to Emitter Voltage	V_{BE}	$I_C=-3.0A$ $V_{CE}=-3.0V$			-2.5	V
Collector output capacitance	C_{ob}	$V_{CB}=-10V$ $I_E=0$ $f=0.1MHz$			300	pF

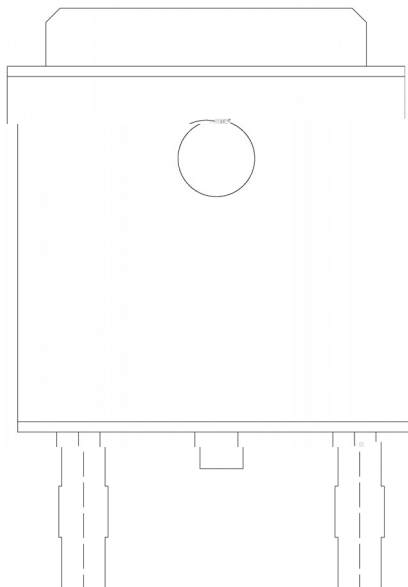
/ Electrical Characteristic Curve



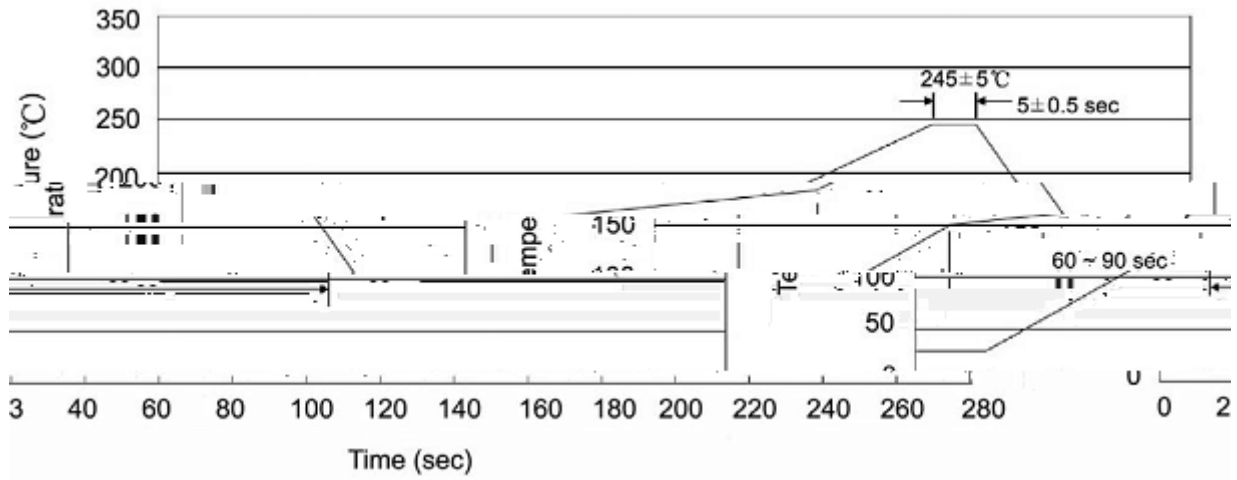
/ Package Dimensions



/ Marking Instructions



() / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

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